



CONFIDENTIAL

#6/Amold R (NE)  
Defect  
10/19/01

Patent  
Attorney's Docket No. 033277-004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )  
Nadim HADDAD et al ) Group Art Unit: 2812  
Application No.: 09/629,172 ) Examiner: R. Pompey  
Filed: July 31, 2000 )  
For: METHOD TO HARDEN SHALLOW )  
TRENCH ISOLATION AGAINST )  
TOTAL IONIZING DOSE RADIATION )

AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

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Date of Deposit 10/15/01  
I do hereby certify that this paper or fee is being  
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20231.  
Richard J. McGrath  
(Typed or printed name of person mailing paper or fee)  
[Signature]  
(Signature of person mailing paper or fee)

Sir:

In response to the Office Action dated July 6, 2001, please amend the above-identified  
patent application as follows:

IN THE CLAIMS:

Please cancel claim 6 and substitute amended claims 1 and 7 as follows:

1. (Amended) A method for fabricating radiation-tolerant integrated circuit devices, said  
method comprising:

depositing a layer of pad oxide on a semiconductor substrate;

selectively etching said pad oxide layer and said semiconductor substrate to define a  
trench within said semiconductor substrate;

implanting boron ions at an angle with respect to normal in said trench; and

implanting an electrically neutral material into said substrate.

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